

Ordering number : ENA0324



SANYO Semiconductors

DATA SHEET

N-Channel Silicon MOSFET
2SK4065 — General-Purpose Switching Device
 Applications

Features

- Ultralow ON-resistance.
- Load switching applications.
- Avalanche resistance guarantee.

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V _{DSS}		75	V
Gate-to-Source Voltage	V _{GSS}		±20	V
Drain Current (DC)	I _D		100	A
Drain Current (Pulse)	I _{DP}	PW≤10μs, duty cycle≤1%	400	A
Allowable Power Dissipation	P _D		1.65	W
		Tc=25°C	90	W
Channel Temperature	T _{ch}		150	°C
Storage Temperature	T _{stg}		-55 to +150	°C
Avalanche Energy (Single Pulse) *1	E _{AS}		735	mJ
Avalanche Current *2	I _{AV}		70	A

Note : *1 V_{DD}=30V, L=200μH, I_{AV}=70A

*2 L≤200μH, Single pulse

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	V(BR)DSS	I _D =1mA, V _{GS} =0V	75			V
Zero-Gate Voltage Drain Current	I _{DSS}	V _{DS} =75V, V _{GS} =0V			1	μA
Gate-to-Source Leakage Current	I _{GSS}	V _{GS} =±16V, V _{DS} =0V			±10	μA
Cutoff Voltage	V _{GS(off)}	V _{DS} =10V, I _D =1mA	1.2		2.6	V
Forward Transfer Admittance	y _{fs}	V _{DS} =10V, I _D =50A	47	78		S
Static Drain-to-Source On-State Resistance	R _{DS(on)1}	I _D =50A, V _{GS} =10V		4.6	6.0	mΩ
	R _{DS(on)2}	I _D =50A, V _{GS} =4V		5.7	8.0	mΩ

Marking : K4065

Continued on next page.

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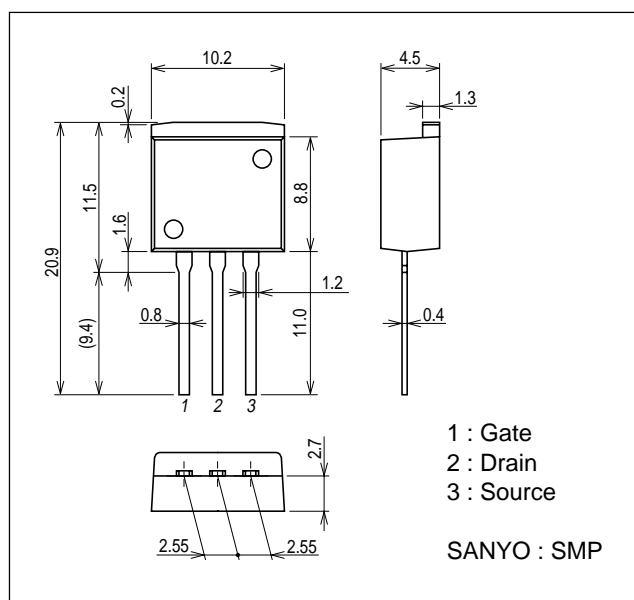
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Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Input Capacitance	Ciss	V _{DS} =20V, f=1MHz		12200		pF
Output Capacitance	Coss	V _{DS} =20V, f=1MHz		950		pF
Reverse Transfer Capacitance	Crss	V _{DS} =20V, f=1MHz		730		pF
Turn-ON Delay Time	t _{d(on)}	See specified Test Circuit.		80		ns
Rise Time	t _r	See specified Test Circuit.		460		ns
Turn-OFF Delay Time	t _{d(off)}	See specified Test Circuit.		930		ns
Fall Time	t _f	See specified Test Circuit.		640		ns
Total Gate Charge	Qg	V _{DS} =35V, V _{GS} =10V, I _D =100A		220		nC
Gate-to-Source Charge	Qgs	V _{DS} =35V, V _{GS} =10V, I _D =100A		40		nC
Gate-to-Drain "Miller" Charge	Qgd	V _{DS} =35V, V _{GS} =10V, I _D =100A		50		nC
Diode Forward Voltage	V _{SD}	I _S =100A, V _{GS} =0V		0.9	1.2	V

Package Dimensions

unit : mm

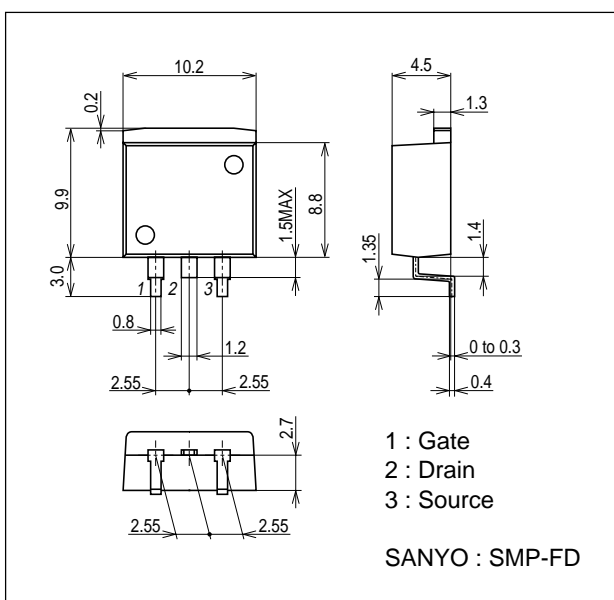
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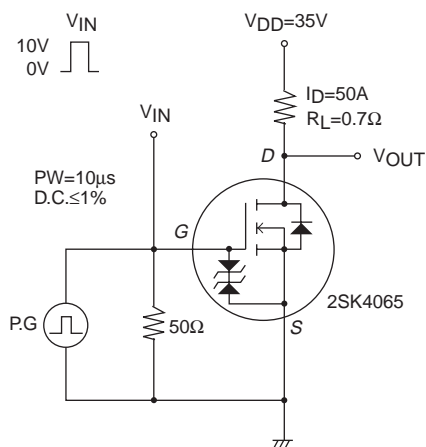
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unit : mm

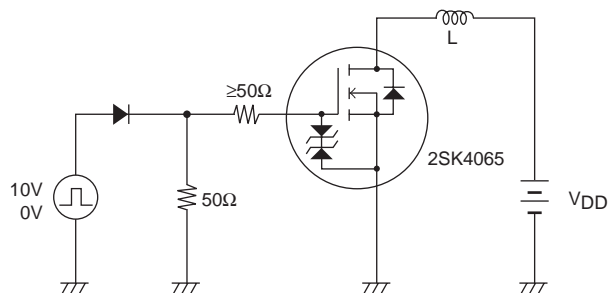
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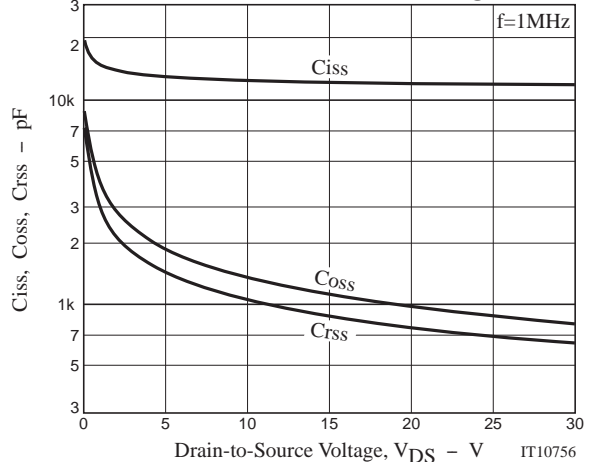
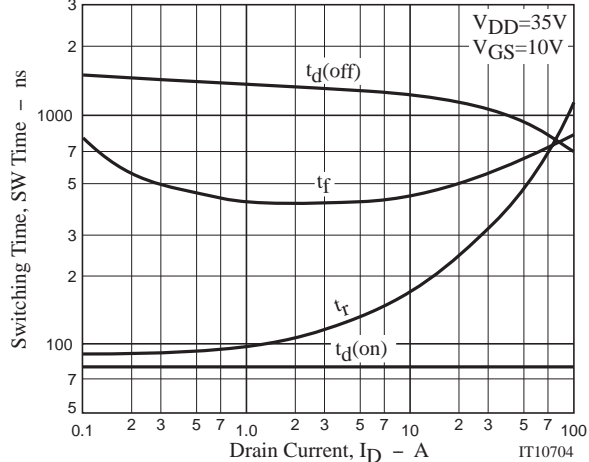
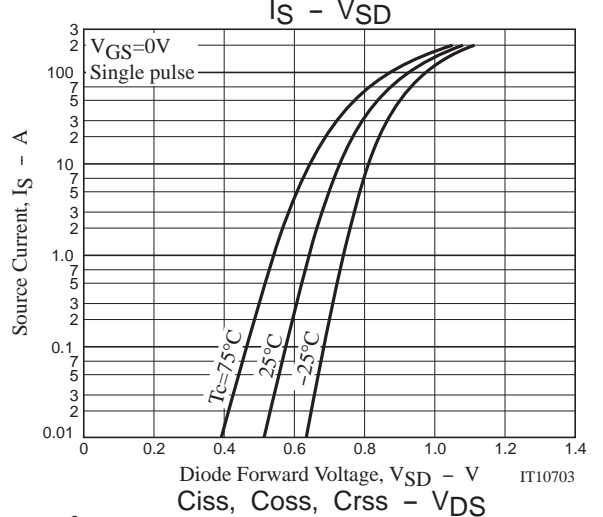
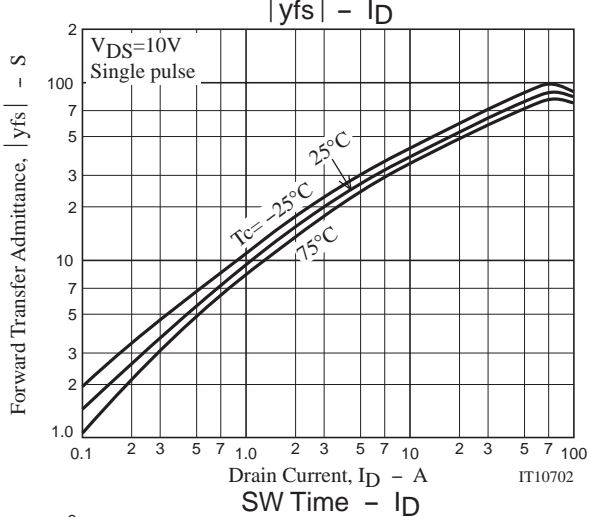
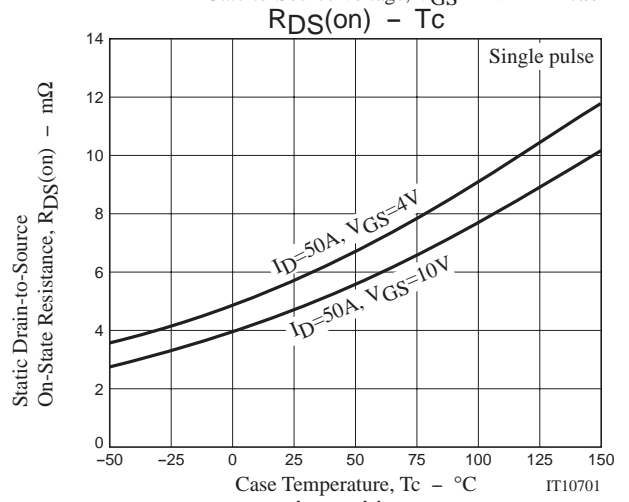
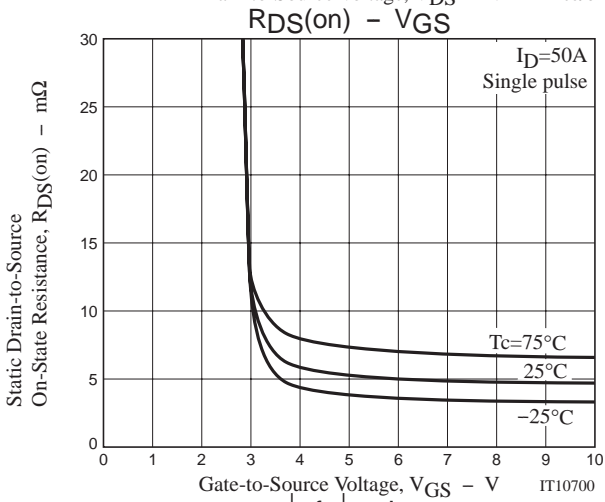
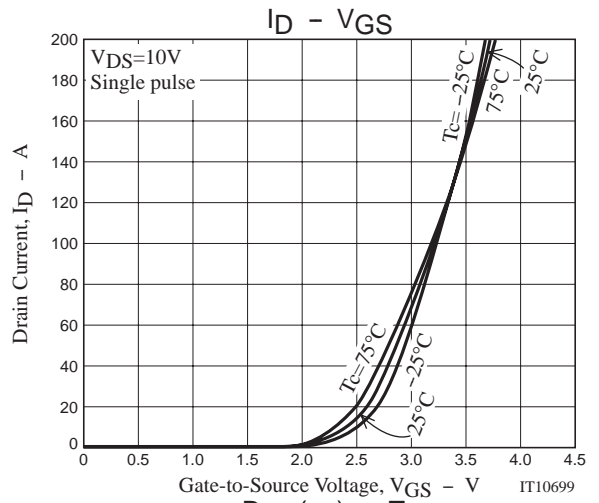
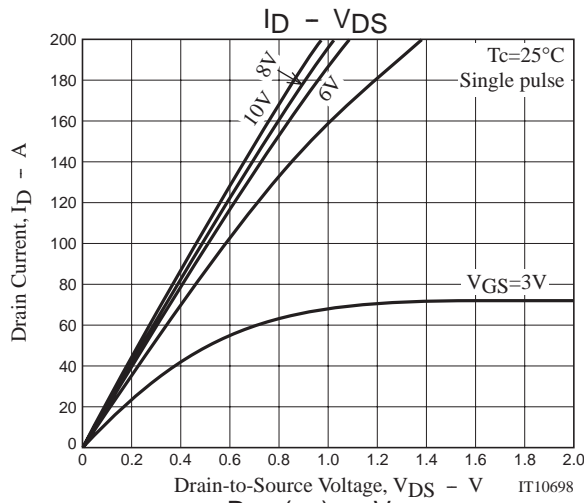
Switching Time Test Circuit



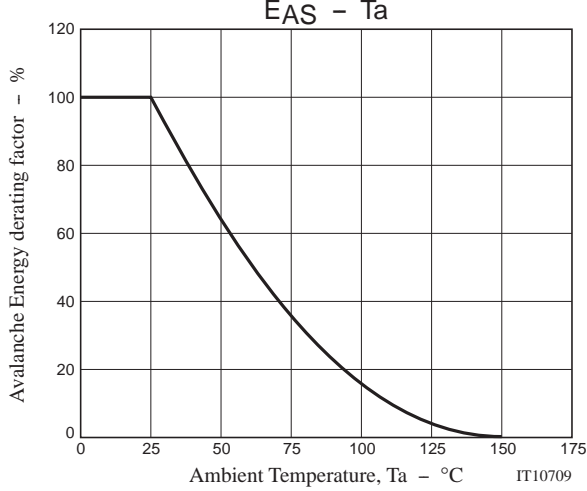
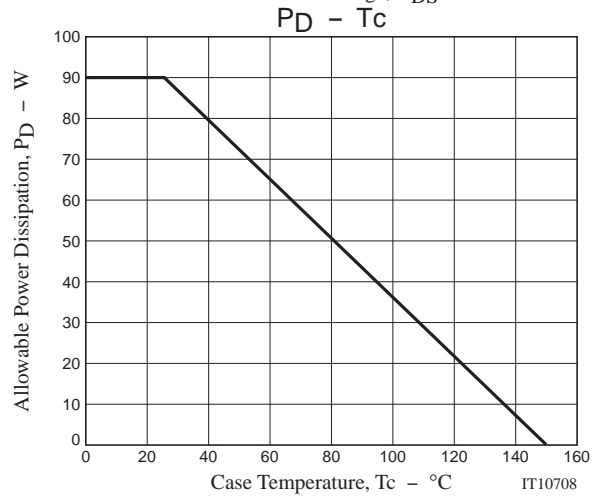
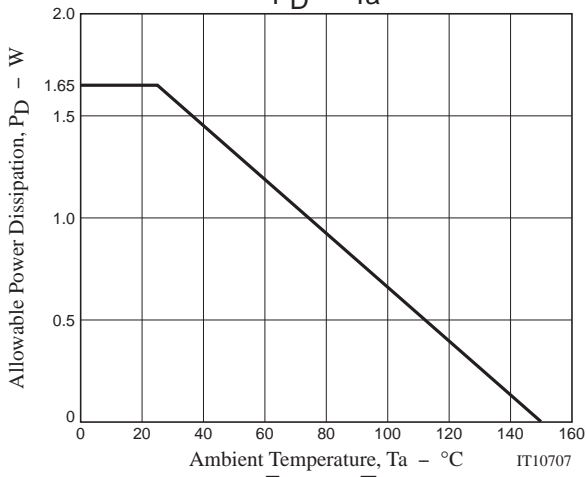
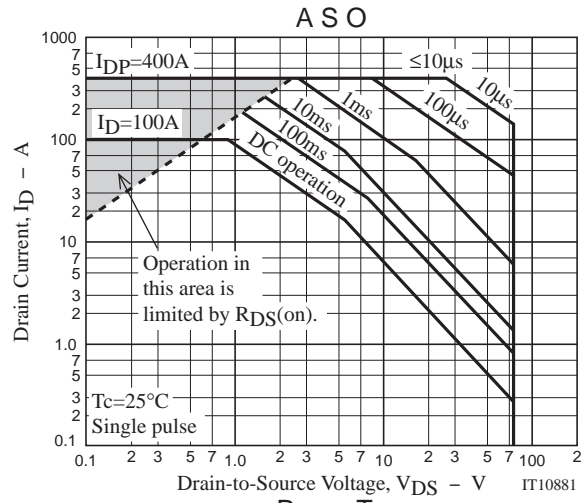
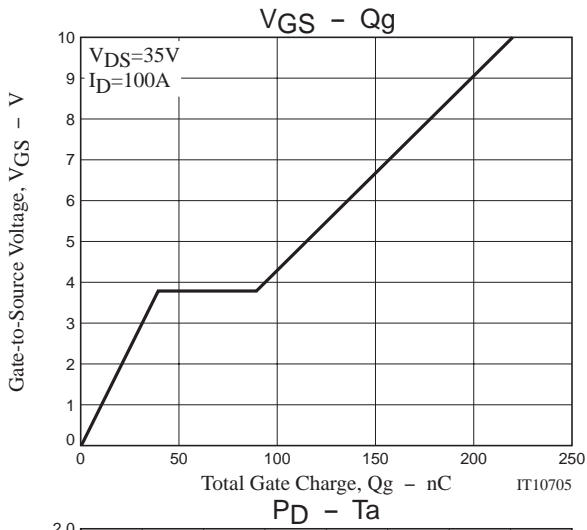
Avalanche Resistance Test Circuit



2SK4065



2SK4065



2SK4065

Note on usage : Since the 2SK4065 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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